

ABSTRACT OF THE DISCLOSURE

A semiconductor device comprising a semiconductor substrate having a recess whose depth is not more than 6 nm, a source region and a drain region which are
5 formed in a surface region of the semiconductor substrate so as to sandwich the recess, each of the source region and the drain region being constituted of an extension region and a contact junction region, a
gate insulating film formed between the source region
10 and the drain region in the semiconductor substrate, and a gate electrode formed on the gate insulating film.